



July 2014

FDMS86202

N-Channel Shielded Gate PowerTrench® MOSFET

120 V, 64 A, 7.2 mΩ

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)} = 7.2 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 13.5 \text{ A}$
- Max $r_{DS(on)} = 10.3 \text{ m}\Omega$ at $V_{GS} = 6 \text{ V}$, $I_D = 11.5 \text{ A}$
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

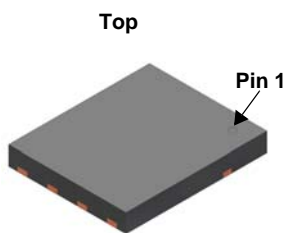


General Description

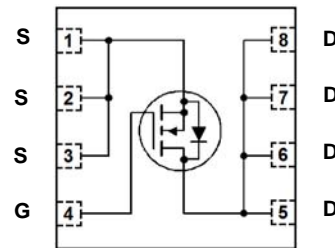
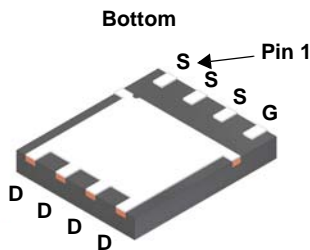
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

Application

- DC-DC Conversion



Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	120	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$	64	A
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	13.5	
	-Pulsed (Note 4)	240	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	600	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	156	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.7	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86202	FDMS86202	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	120			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		103		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 96\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	3.1	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		-10		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 13.5\text{ A}$		6.0	7.2	m Ω
		$V_{GS} = 6\text{ V}$, $I_D = 11.5\text{ A}$		8.1	10.3	
		$V_{GS} = 10\text{ V}$, $I_D = 13.5\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		10.9	13.2	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 13.5\text{ A}$		44		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		3195	4250	pF
C_{oss}	Output Capacitance			449	600	pF
C_{rss}	Reverse Transfer Capacitance			17	30	pF
R_g	Gate Resistance		0.1	0.9	2.7	Ω

Switching Characteristics

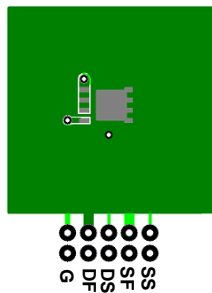
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 60\text{ V}$, $I_D = 13.5\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		21	33	ns
t_r	Rise Time			6	13	ns
$t_{d(off)}$	Turn-Off Delay Time			27	44	ns
t_f	Fall Time			5	11	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	$V_{DD} = 60\text{ V}$, $I_D = 13.5\text{ A}$	45	64	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 6 V		29	41	nC
Q_{gs}	Gate to Source Charge			14.3		nC
Q_{gd}	Gate to Drain "Miller" Charge			8.7		nC

Drain-Source Diode Characteristics

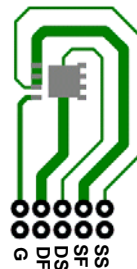
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2.1\text{ A}$ (Note 2)		0.69	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 13.5\text{ A}$ (Note 2)		0.76	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 13.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		73	118	ns
Q_{rr}	Reverse Recovery Charge			117	187	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 45 $^{\circ}\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) 115 $^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. E_{AS} of 600 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 20\text{ A}$, $V_{DD} = 120\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 65\text{ A}$.

4. Pulse I_d limited by junction temperature, $t_d \leq 100\text{ }\mu\text{s}$, please refer to SOA curve for more details.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

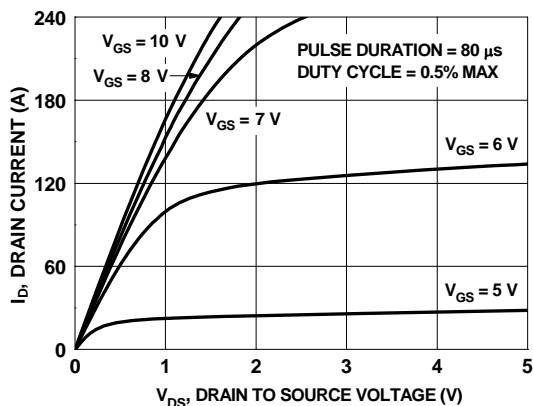


Figure 1. On Region Characteristics

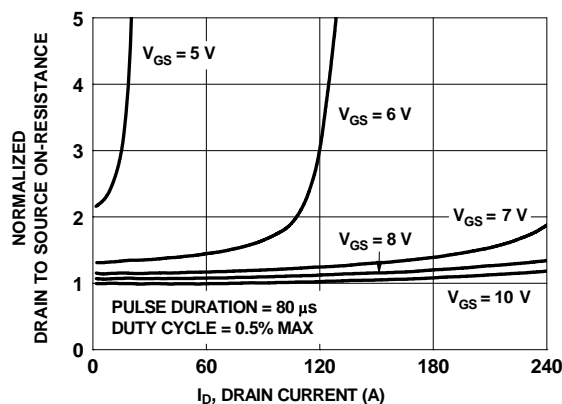


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

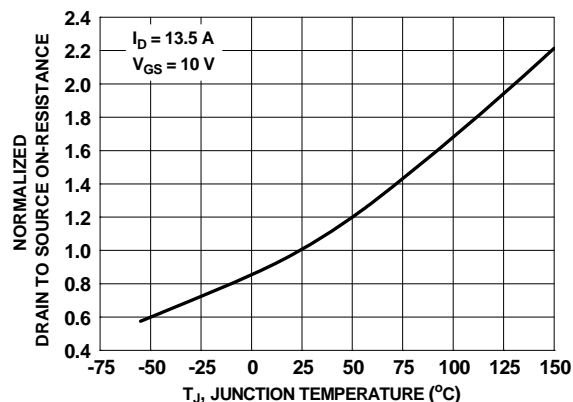


Figure 3. Normalized On Resistance vs Junction Temperature

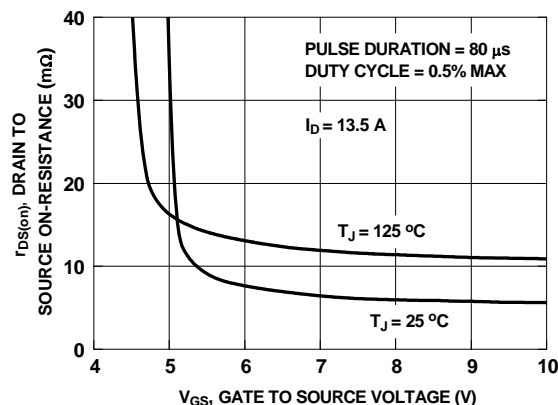


Figure 4. On-Resistance vs Gate to Source Voltage

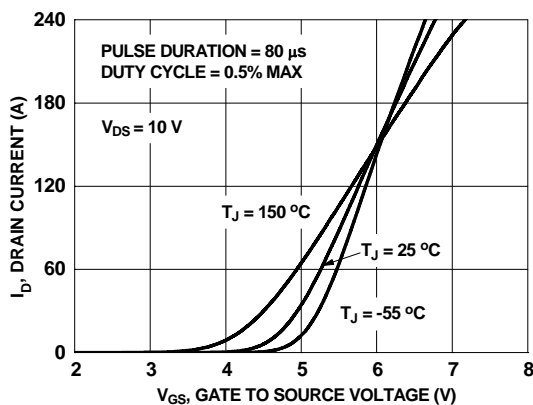


Figure 5. Transfer Characteristics

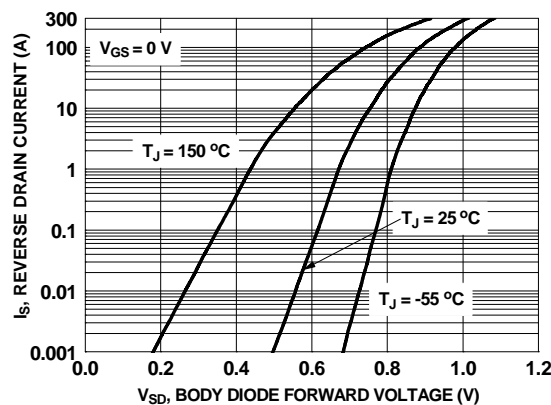


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

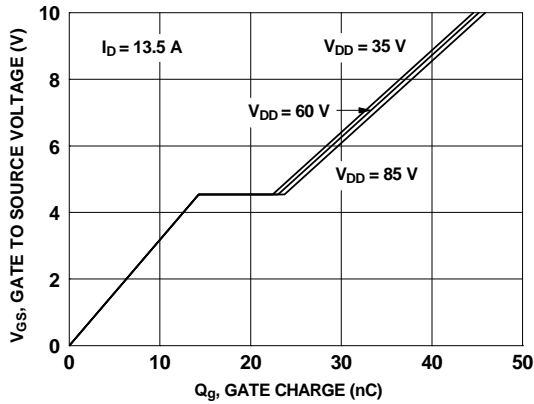


Figure 7. Gate Charge Characteristics

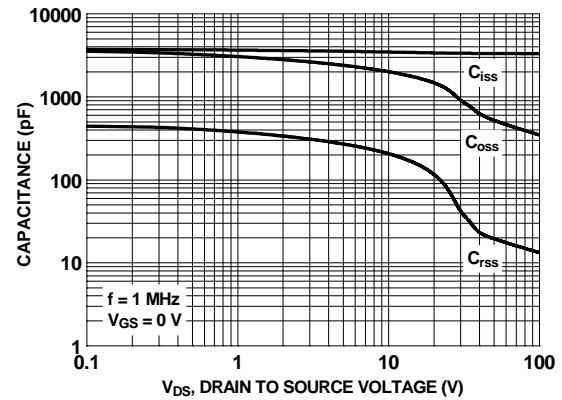


Figure 8. Capacitance vs Drain to Source Voltage

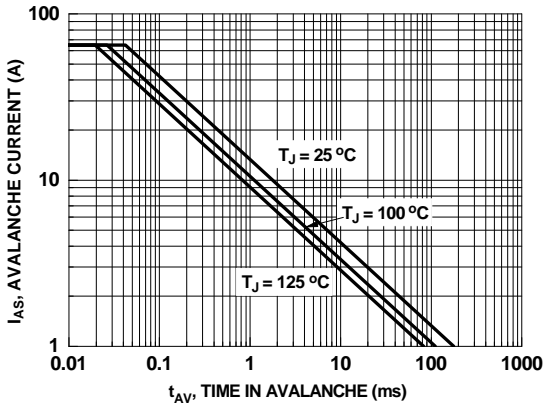


Figure 9. Unclamped Inductive Switching Capability

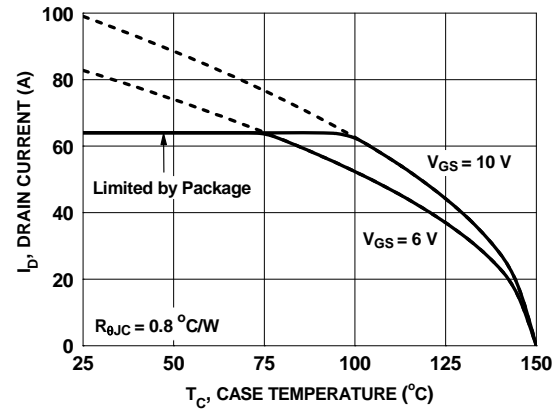


Figure 10. Maximum Continuous Drain Current vs Case Temperature

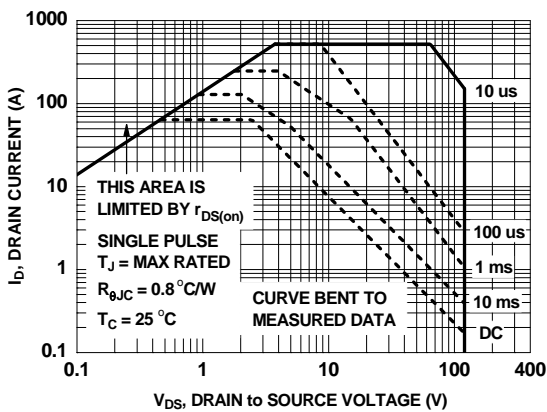


Figure 11. Forward Bias Safe Operating Area

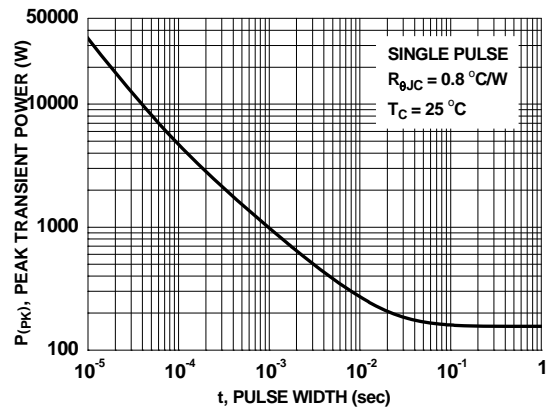


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

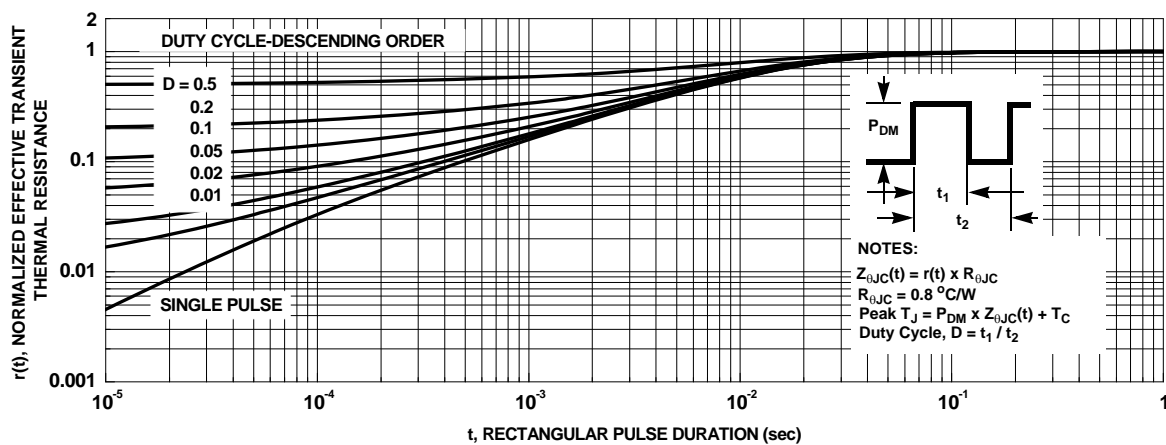
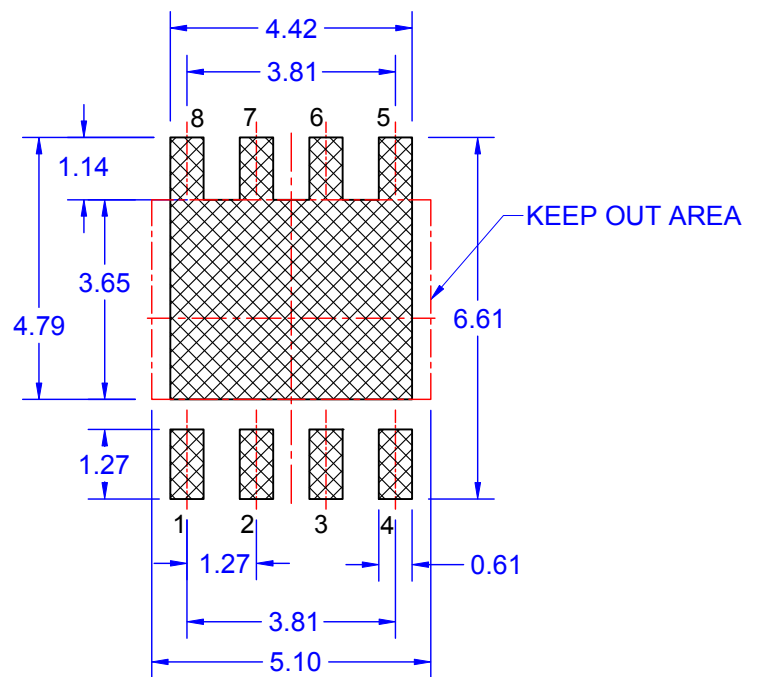
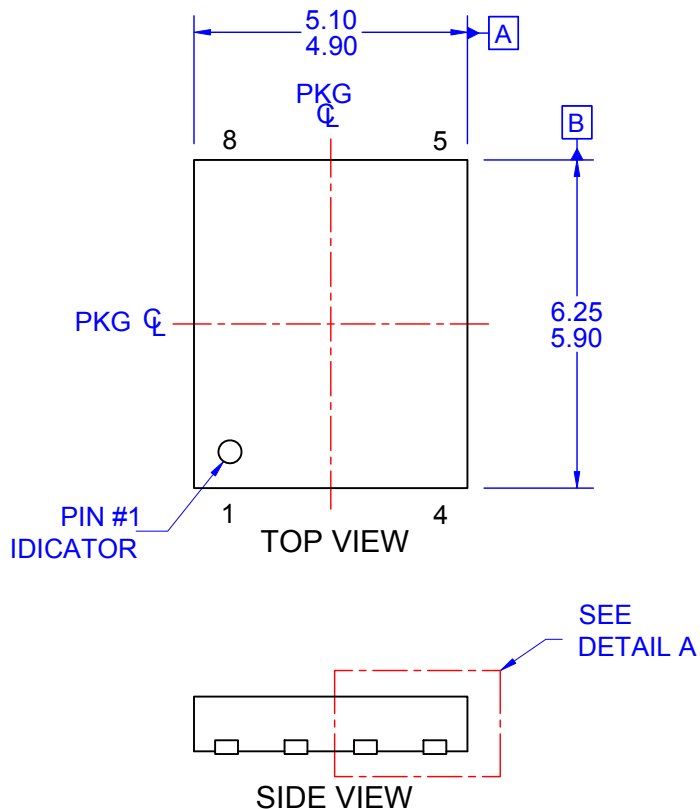
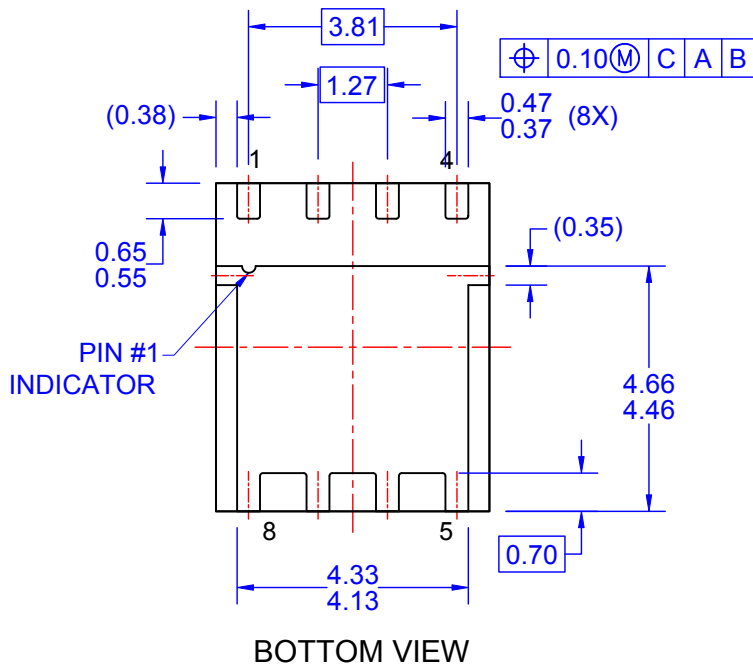


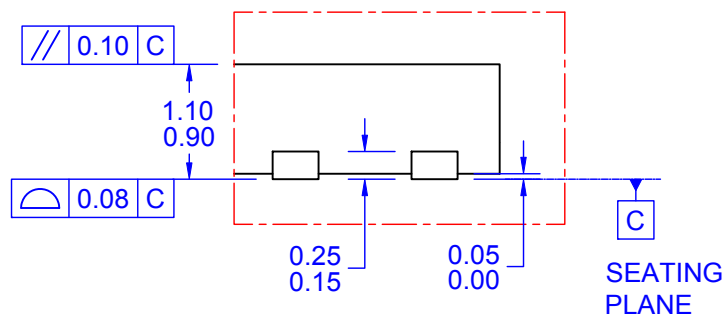
Figure 13. Junction-to-Case Transient Thermal Response Curve



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RECOMMENDATION



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- A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
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DETAIL A

SCALE: 2:1



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